

L Number	Hits	Search Text	DB	Time stamp
-	19	(SiON or "silicon oxynitride") and ("tetramethyl ammonium hydroxide" or TMAH) and ("isopropyl alcohol" or IPA)	USPAT; US-PGPUB	2003/04/24 12:02
-	16	((SiON or "silicon oxynitride") and ("tetramethyl ammonium hydroxide" or TMAH) and ("isopropyl alcohol" or IPA)) not (@ad>20020109 or @rlad>20020109)	USPAT; US-PGPUB	2003/04/15 11:42
-	5	((SiON or "silicon oxynitride") and ("tetramethyl ammonium hydroxide" or TMAH) and ("isopropyl alcohol" or IPA)) not (@ad>20020109 or @rlad>20020109)) and 438/\$.ccls.	USPAT; US-PGPUB	2003/04/09 15:50
-	182	(SiON or "silicon oxynitride") and ("tetramethyl ammonium hydroxide" or TMAH)	USPAT; US-PGPUB	2003/04/24 12:02
-	507	(SiON or "silicon oxynitride") and ("isopropyl alcohol" or IPA)	USPAT; US-PGPUB	2003/04/09 15:50
-	0	438/692.ccls. and ((SiON or "silicon oxynitride") and ("tetramethyl ammonium hydroxide" or TMAH))	USPAT; US-PGPUB	2003/04/09 15:50
-	1	438/692.ccls. AND ((SiON or "silicon oxynitride") and ("isopropyl alcohol" or IPA))	USPAT; US-PGPUB	2003/04/09 15:52
-	89	438/749.ccls.	USPAT; US-PGPUB	2003/04/09 15:53
-	1	((SiON or "silicon oxynitride") and ("tetramethyl ammonium hydroxide" or TMAH)) and 438/749.ccls.	USPAT; US-PGPUB	2003/04/09 15:54
-	0	((SiON or "silicon oxynitride") and ("isopropyl alcohol" or IPA)) and 438/749.ccls.	USPAT; US-PGPUB	2003/04/09 15:54
-	160	438/750.ccls.	USPAT; US-PGPUB	2003/04/09 15:55
-	0	((SiON or "silicon oxynitride") and ("tetramethyl ammonium hydroxide" or TMAH)) and 438/750.ccls.	USPAT; US-PGPUB	2003/04/09 15:55
-	0	((SiON or "silicon oxynitride") and ("isopropyl alcohol" or IPA)) and 438/750.ccls.	USPAT; US-PGPUB	2003/04/09 15:55
-	110	438/751.ccls.	USPAT; US-PGPUB	2003/04/09 15:55
-	0	((SiON or "silicon oxynitride") and ("isopropyl alcohol" or IPA)) and 438/751.ccls.	USPAT; US-PGPUB	2003/04/09 15:55
-	1	((SiON or "silicon oxynitride") and ("tetramethyl ammonium hydroxide" or TMAH)) and 438/751.ccls.	USPAT; US-PGPUB	2003/04/09 15:56
-	361	438/906.ccls.	USPAT; US-PGPUB	2003/04/09 15:56
-	0	((SiON or "silicon oxynitride") and ("tetramethyl ammonium hydroxide" or TMAH)) and 438/906.ccls.	USPAT; US-PGPUB	2003/04/09 15:56
-	2	((SiON or "silicon oxynitride") and ("isopropyl alcohol" or IPA)) and 438/906.ccls.	USPAT; US-PGPUB	2003/04/09 16:03
-	293	438/974.ccls.	USPAT; US-PGPUB	2003/04/09 16:03
-	0	((SiON or "silicon oxynitride") and ("tetramethyl ammonium hydroxide" or TMAH)) and 438/974.ccls.	USPAT; US-PGPUB	2003/04/09 16:03
-	0	((SiON or "silicon oxynitride") and ("isopropyl alcohol" or IPA)) and 438/974.ccls.	USPAT; US-PGPUB	2003/04/09 16:03
-	821	(SiON or "silicon oxynitride") and hydrophobic	USPAT; US-PGPUB	2003/04/09 16:04
-	86	438/\$.ccls. and ((SiON or "silicon oxynitride") and hydrophobic)	USPAT; US-PGPUB	2003/04/09 16:04
-	72	(438/\$.ccls. and ((SiON or "silicon oxynitride") and hydrophobic)) not (@ad>20020109 or @rlad>20020109)	USPAT; US-PGPUB	2003/04/09 16:04
-	43622	platen	USPAT; US-PGPUB	2003/04/09 16:04
-	1	((438/\$.ccls. and ((SiON or "silicon oxynitride") and hydrophobic)) not (@ad>20020109 or @rlad>20020109)) and platen	USPAT; US-PGPUB	2003/04/09 16:05
-	5	(SiON or "silicon oxynitride") and ("tetramethyl ammonium hydroxide" or TMAH) and platen	USPAT; US-PGPUB	2003/04/09 16:07
-	5	((SiON or "silicon oxynitride") and ("tetramethyl ammonium hydroxide" or TMAH) and platen) not (@ad>20020109 or @rlad>20020109)	USPAT; US-PGPUB	2003/04/09 16:05
-	10	(SiON or "silicon oxynitride") and ("isopropyl alcohol" or IPA) and platen	USPAT; US-PGPUB	2003/04/09 16:07

	9	((SiON or "silicon oxynitride") and ("isopropyl alcohol" or IPA) and platen) not (@ad>20020109 or @rlad>20020109)	USPAT;	2003/04/09
	24	438/for.111.ccls.	US-PGPUB EPO; JPO; DERWENT	17:01 2003/04/10 09:54
	571	remov\$3 with (SiON or "silicon oxynitride")	USPAT;	2003/04/10 10:42
	19	(remov\$3 with (SiON or "silicon oxynitride")) and ("tetramethyl ammonium hydroxide" or TMAH)	USPAT;	2003/04/10 10:43
	17	((remov\$3 with (SiON or "silicon oxynitride")) and ("tetramethyl ammonium hydroxide" or TMAH)) not (@ad>20020109 or @rlad>20020109)	USPAT;	2003/04/15 11:57
	4	(remov\$3 with (SiON or "silicon oxynitride")) and ("isopropyl alcohol" or IPA)	USPAT;	2003/04/10 10:46
	4	((remov\$3 with (SiON or "silicon oxynitride")) and ("isopropyl alcohol" or IPA)) not (@ad>20020109 or @rlad>20020109)	USPAT;	2003/04/15 11:57
	14469	(polish\$3 or CMP) with (partial or partially or thickness)	USPAT; US-PGPUB USPAT; US-PGPUB USPAT; US-PGPUB USPAT; US-PGPUB	2003/04/15 11:59
	391	438/626.ccls.	USPAT; US-PGPUB USPAT; US-PGPUB	2003/04/15 11:37
	73	((polish\$3 or CMP) with (partial or partially or thickness)) and 438/626.ccls.	USPAT;	2003/04/15 11:38
	20	((SiON or "silicon oxynitride") and (((polish\$3 or CMP) with (partial or partially or thickness)) and 438/626.ccls.)	USPAT;	2003/04/15 11:38
	o	((SiON or "silicon oxynitride") with ("tetramethyl ammonium hydroxide" or TMAH) and ("isopropyl alcohol" or IPA)) not (@ad>20020109 or @rlad>20020109)	USPAT; US-PGPUB	2003/04/15 12:00
	o	((SiON or "silicon oxynitride") same ("tetramethyl ammonium hydroxide" or TMAH) and ("isopropyl alcohol" or IPA)) not (@ad>20020109 or @rlad>20020109)	USPAT; US-PGPUB	2003/04/15 11:43
	16	((SiON or "silicon oxynitride") and ("tetramethyl ammonium hydroxide" or TMAH) and ("isopropyl alcohol" or IPA)) not (@ad>20020109 or @rlad>20020109)	USPAT; US-PGPUB	2003/04/15 11:49
	o	((polish\$3 or CMP) with (partial or partially or thickness)) and (((SiON or "silicon oxynitride") and ("tetramethyl ammonium hydroxide" or TMAH) and ("isopropyl alcohol" or IPA)) not (@ad>20020109 or @rlad>20020109))	USPAT; US-PGPUB	2003/04/15 11:43
	44880	((SiON or "silicon oxynitride") and ("tetramethyl ammonium hydroxide" or TMAH) or ("isopropyl alcohol" or IPA)) not (@ad>20020109 or @rlad>20020109)	USPAT; US-PGPUB	2003/04/15 11:44
	375	((polish\$3 or CMP) with (partial or partially or thickness)) and (((SiON or "silicon oxynitride") and ("tetramethyl ammonium hydroxide" or TMAH) or ("isopropyl alcohol" or IPA)) not (@ad>20020109 or @rlad>20020109))	USPAT; US-PGPUB	2003/04/15 11:44
	23	((SiON or "silicon oxynitride") and (((polish\$3 or CMP) with (partial or partially or thickness)) and (((SiON or "silicon oxynitride") and ("tetramethyl ammonium hydroxide" or TMAH) or ("isopropyl alcohol" or IPA)) not (@ad>20020109 or @rlad>20020109))))	USPAT; US-PGPUB	2003/04/15 11:47
	582	438/633.ccls.	USPAT; US-PGPUB	2003/04/15 11:47
	47	((polish\$3 or CMP) with (partial or partially or thickness)) and (SiON or "silicon oxynitride") and 438/633.ccls.	USPAT; US-PGPUB	2003/04/15 11:47
	50081	("tetramethyl ammonium hydroxide" or TMAH) or ("isopropyl alcohol" or IPA)	USPAT; US-PGPUB	2003/04/15 11:50
	1	((polish\$3 or CMP) with (partial or partially or thickness)) and (SiON or "silicon oxynitride") and 438/633.ccls.) and ("tetramethyl ammonium hydroxide" or TMAH) or ("isopropyl alcohol" or IPA))	USPAT; US-PGPUB	2003/04/15 11:51
	1429	438/692.ccls.	USPAT; US-PGPUB	2003/04/15 11:51
	1	("tetramethyl ammonium hydroxide" or TMAH) or ("isopropyl alcohol" or IPA) and (((polish\$3 or CMP) with (partial or partially or thickness)) and (SiON or "silicon oxynitride") and 438/692.ccls.)	USPAT; US-PGPUB	2003/04/15 11:51
	41	((polish\$3 or CMP) with (partial or partially or thickness)) and (SiON or "silicon oxynitride") and 438/692.ccls.	USPAT; US-PGPUB	2003/04/15 11:55

	751	438/672.ccls.	USPAT; US-PGPUB	2003/04/15 11:55
	o	((("tetramethyl ammonium hydroxide" or TMAH) or ("isopropyl alcohol" or IPA)) and (((polish\$3 or CMP) with (partial or partially or thickness)) and (SiON or "silicon oxynitride") and 438/672.ccls.)	USPAT; US-PGPUB	2003/04/15 11:55
	17	((polish\$3 or CMP) with (partial or partially or thickness)) and (SiON or "silicon oxynitride") and 438/672.ccls.	USPAT; US-PGPUB	2003/04/15 11:55
	o	((remov\$3 with (SiON or "silicon oxynitride")) with ("isopropyl alcohol" or IPA)) not (@ad>20020109 or @rlad>20020109)	USPAT; US-PGPUB	2003/04/15 11:58
	o	((remov\$3 with (SiON or "silicon oxynitride")) with ("tetramethyl ammonium hydroxide" or TMAH)) not (@ad>20020109 or @rlad>20020109)	USPAT; US-PGPUB	2003/04/15 11:59
	1201	438/for.355.ccls.	EPO; JPO; DERWENT; IBM_TDB	2003/04/15 11:58
	o	((remov\$3 with (SiON or "silicon oxynitride")) with ("isopropyl alcohol" or IPA)) not (@ad>20020109 or @rlad>20020109)	EPO; JPO; DERWENT; IBM_TDB	2003/04/15 11:59
	o	((remov\$3 with (SiON or "silicon oxynitride")) with ("tetramethyl ammonium hydroxide" or TMAH)) not (@ad>20020109 or @rlad>20020109)	EPO; JPO; DERWENT; IBM_TDB	2003/04/15 11:59
	5910	(polish\$3 or CMP) with (partial or partially or thickness)	EPO; JPO; DERWENT; IBM_TDB	2003/04/15 11:59
	2	438/for.355.ccls. and ((polish\$3 or CMP) with (partial or partially or thickness))	EPO; JPO; DERWENT; IBM_TDB	2003/04/15 11:59
	6548	(SiON or "silicon oxynitride") with ("tetramethyl ammonium hydroxide" or TMAH)or ("isopropyl alcohol" or IPA)	EPO; JPO; DERWENT; IBM_TDB	2003/04/15 12:05
	o	438/for.355.ccls. and ((SiON or "silicon oxynitride") with ("tetramethyl ammonium hydroxide" or TMAH)or ("isopropyl alcohol" or IPA))	EPO; JPO; DERWENT; IBM_TDB	2003/04/15 12:00
	8	((polish\$3 or CMP) with (partial or partially or thickness)) and ((SiON or "silicon oxynitride") with ("tetramethyl ammonium hydroxide" or TMAH)or ("isopropyl alcohol" or IPA))	EPO; JPO; DERWENT; IBM_TDB	2003/04/15 12:04
	952640	semiconductor or "integrated circuit"	EPO; JPO; DERWENT; IBM_TDB	2003/04/15 12:04
	569	((SiON or "silicon oxynitride") with ("tetramethyl ammonium hydroxide" or TMAH)or ("isopropyl alcohol" or IPA)) and (semiconductor or "integrated circuit")	EPO; JPO; DERWENT; IBM_TDB	2003/04/15 12:04
	3644	SiON or "silicon oxynitride"	EPO; JPO; DERWENT; IBM_TDB	2003/04/15 12:05
	o	(((SiON or "silicon oxynitride") with ("tetramethyl ammonium hydroxide" or TMAH)or ("isopropyl alcohol" or IPA)) and (semiconductor or "integrated circuit")) and (SiON or "silicon oxynitride")	EPO; JPO; DERWENT; IBM_TDB	2003/04/15 12:05
	13466	SiON or "silicon oxynitride"	USPAT; US-PGPUB	2003/04/24 12:02
	1824548	remov\$3 or etch\$3	USPAT; US-PGPUB	2003/04/24 12:21
	1918183	remov\$3 or etch\$3 or clean\$3	USPAT; US-PGPUB	2003/04/24 12:21
	1655	(SiON or "silicon oxynitride") with (remov\$3 or etch\$3 or clean\$3)	USPAT; US-PGPUB	2003/04/24 12:13
	1474	((SiON or "silicon oxynitride") with (remov\$3 or etch\$3 or clean\$3)) not (@ad>20020109 or @rlad>20020109)	USPAT; US-PGPUB	2003/04/24 12:14
	64587	438/\$.ccls.	USPAT; US-PGPUB	2003/04/24 12:15
	1055	(((SiON or "silicon oxynitride") with (remov\$3 or etch\$3 or clean\$3)) not (@ad>20020109 or @rlad>20020109)) and 438/\$.ccls.	USPAT; US-PGPUB	2003/04/24 12:18

	1436	438/692.ccls.	USPAT; US-PGPUB	2003/04/24 12:16
	32	((SiON or "silicon oxynitride") with (remov\$3 or etch\$3 or clean\$3) not (@ad>20020109 or @rlad>20020109)) and 438/\$.ccls.) and 438/692.ccls.	USPAT; US-PGPUB	2003/04/24 12:16
	4401	"tetramethyl ammonium hydroxide" or TMAH	USPAT; US-PGPUB	2003/04/24 12:17
	46457	"isopropyl alcohol" or IPA	USPAT; US-PGPUB	2003/04/24 12:17
	o	((SiON or "silicon oxynitride") with (remov\$3 or etch\$3 or clean\$3) not (@ad>20020109 or @rlad>20020109)) with ("tetramethyl ammonium hydroxide" or TMAH)	USPAT; US-PGPUB	2003/04/24 12:18
	o	((SiON or "silicon oxynitride") with (remov\$3 or etch\$3 or clean\$3) not (@ad>20020109 or @rlad>20020109)) with ("isopropyl alcohol" or IPA)	USPAT; US-PGPUB	2003/04/24 12:18
	98856	hydrophobic	USPAT; US-PGPUB	2003/04/24 12:19
	3	((SiON or "silicon oxynitride") with (remov\$3 or etch\$3 or clean\$3) not (@ad>20020109 or @rlad>20020109)) with hydrophobic	USPAT; US-PGPUB	2003/04/24 12:20
	remov\$3		USPAT; US-PGPUB	2003/04/24 12:22
	1780212		USPAT; US-PGPUB	2003/04/24 12:22
	582	(SiON or "silicon oxynitride") with remov\$3	USPAT; US-PGPUB	2003/04/24 12:22
	532	((SiON or "silicon oxynitride") with remov\$3 ) not (@ad>20020109 or @rlad>20020109)	USPAT; US-PGPUB	2003/04/24 12:22
	13466	SiON or "silicon oxynitride"	USPAT; US-PGPUB	2003/04/24 12:24
	1780212	remov\$3	USPAT; US-PGPUB	2003/04/24 12:24
	944483	slurry or solution	USPAT; US-PGPUB	2003/04/24 12:25
	964464	W or tungsten	USPAT; US-PGPUB	2003/04/24 14:07
	46	(SiON or "silicon oxynitride") with remov\$3 with (slurry or solution)	USPAT; US-PGPUB	2003/04/24 14:25
	2	(W or tungsten) with ((SiON or "silicon oxynitride") with remov\$3 with (slurry or solution))	USPAT; US-PGPUB	2003/04/24 14:07
	123	conductive and dielectric and "silicon oxynitride" and "titanium nitride" and (via or hole or opening or trench) and tungsten and CMP and slurry	USPAT; US-PGPUB	2003/04/24 14:27
	107822	@ad>20020109 or @rlad>20020109	USPAT; US-PGPUB	2003/04/24 14:28
	113	(conductive and dielectric and "silicon oxynitride" and "titanium nitride" and (via or hole or opening or trench) and tungsten and CMP and slurry ) not (@ad>20020109 or @rlad>20020109)	USPAT; US-PGPUB	2003/04/24 14:54
	449	platen with "polishing pad" with slurry	USPAT; US-PGPUB	2003/04/24 15:47
	o	((SiON or "silicon oxynitride") with remov\$3 with (slurry or solution)) and (platen with "polishing pad" with slurry )	USPAT; US-PGPUB	2003/04/24 15:47
	2	(conductive and dielectric and "silicon oxynitride" and "titanium nitride" and (via or hole or opening or trench) and tungsten and CMP and slurry ) and (platen with "polishing pad" with slurry )	USPAT; US-PGPUB	2003/04/24 15:48